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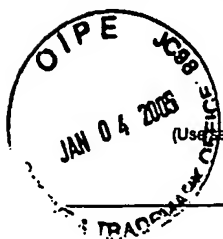
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U.S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent pages, etc.)

EP	"Low-temperature growth of piezoelectric AlN film by rf reactive planar magnetron sputtering", T. Shiosaki et al., Appl. Phys. Lett. 36(8), 15 April 1980, 643-645, © 1980 American Institute of Physics
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EP	"Structural properties of AlN films grown on Si, Ru/Si and ZnO/Si substrates", Won Taeg Lim et al., Thin solid Films 382(2001) 56-60, © 2001 Elsevier Science
EP	"Synthesis and Surface Acoustic Wave Property of Aluminum Nitride Thin films Fabricated on Silicon and Diamond Substrates Using the Sputtering Method", M. Ishihara et al., Jpn. J. Appl. Phys, vol. 40(2001) pp. 5065-5068 Part 1, No. 8, August, © 2001 The Japan Society of Applied Physics
EP	"Deposition of AlN thin film using reactive sputtering method", Y. Honda et al., Reports of Kumamoto Industrial Research Institute No. 35, 1997, pp. 59-63 © Kumamoto Industrial Research Institute

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